## Compositionally Variant Bimetallic Cu-Mn Oxysulfide Electrodes with Meritorious Supercapacitive Performance and High Energy Density

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Figure S1: XRD patterns of (a)  $C_1M_3OS$ , (b)  $C_1M_1OS$ , and (c)  $C_3M_1OS$  nanocomposites with their corresponding reference cards.



Figure S2: X-ray photoelectron spectroscopy survey scan of the C<sub>3</sub>M<sub>1</sub>OS nanocomposite.



**Figure S3:** Three-electrode electrochemical measurements: (a) CV profile of  $C_1M_1OS$  at various scan rates (5–100 mV/s), The reliance of cathodic and anodic currents on the applied scan rate for (b)  $C_1M_1OS$ , (c)  $C_1M_3OS$ , and (d) specific capacitance recorded at different several scan rates for  $C_1M_3OS$ ,  $C_1M_1OS$ , and  $C_3M_1OS$  electrodes in 2 M KOH.

The electrochemical active surface area (ECSA) was calculated from a series of cyclic voltammograms in the non-faradaic region at different scan rates (3–100 mV/s), as shown in Fig.

7a. The ECSA values can be obtained using the equation  $ECSA = \frac{C_{DL}}{C_s}$ , where Cs is the specific capacitance of a flat surface of the material per unit area. This specific capacitance is usually between 20 and 60 µF/cm<sup>2</sup> for metal-based materials in alkaline electrolytes; the average value of 40 µF/cm<sup>2</sup> is usually used and Cdl is the electrochemical double-layer capacitance of the Flat surface. <sup>1–3</sup> Based on the obtained Cdl values from the slopes in **Figure S4 b,d,f**, the ESCA was found to be 32, 25, and 17 cm<sup>2</sup> C<sub>3</sub>M<sub>1</sub>OS, C<sub>1</sub>M<sub>1</sub>OS, and C<sub>1</sub>M<sub>3</sub>OS electrodes , respectively. Confirming the superior activity of the fabricated composites and the outstanding electrochemical performance of the C<sub>3</sub>M<sub>1</sub>OS electrode.



**Figure S4:** The electrochemical surface area measurements: cyclic voltammograms at different scan rates (3-100) mV/s, anodic and cathodic currents as a function of scan rate of the (a, b) C<sub>3</sub>M<sub>1</sub>OS, (c, d) C<sub>1</sub>M<sub>1</sub>OS, and (e, f) C<sub>1</sub>M<sub>3</sub>OS electrodes.



**Figure S5:** Three-electrode electrochemical measurements: (a) specific capacity of the  $C_1M_3OS$ ,  $C_1M_1OS$ ,  $C_3M_1OS$  and  $C_4M_0OS$  electrodes at a current density of 1 A/g. (b) CV profiles at various scan rates (5–100 mV/s), and (c) GCD profiles at various current densities (2–10 A/g) of  $C_4M_0OS$  electrode.



**Figure S6:** Three-electrode electrochemical measurements: (a) specific capacity of the  $C_1M_3OS$ ,  $C_1M_1OS$ ,  $C_3M_1OS$ ,  $C_4M_0OS$  and  $C_0M_4OS$  electrodes at a current density of 1 A/g. (b) CV profiles at various scan rates (5–100 mV/s), and (c) GCD profiles at various current densities (2–10 A/g) of  $C_0M_4OS$  electrode.

## Material characterization of C<sub>3</sub>M<sub>1</sub>OS electrode after cycling

As for the morphology of the electrode after cycling, SEM image (**Figure S7a**) showed the retaining of the nanocube-like structure covered with nanoneedles with the presence of some aggregates. Additionally, EDX and XPS analysis shown in **Figure S7b,c** confirmed the presence of all chemical elements (Cu, Mn, S, and O) after cycling, demonstrating the stability of the C<sub>3</sub>M<sub>1</sub>OS electrode.



**Figure S7**: (a) field-emission scanning electron microscopy (FESEM) image, (b) the EDX spectrum and (c) X-ray photoelectron spectroscopy survey scan of  $C_3M_1OS$  electrode after cycling.



**Figure S8:** Electrochemical characteristics of  $C_3M_1OS//AC$  asymmetric device: (a) Nyquist plots for the designed device.

## Table S1 Bader net atomic charge

Element	C <sub>1</sub> M <sub>3</sub> OS	C <sub>1</sub> M <sub>1</sub> OS	C <sub>3</sub> M <sub>1</sub> OS
Cu	0.413269	0.480593	0.514096
Cu		0.490029	0.532672
Cu			0.895732
Mn	1.041738	1.61466	1.75898
Mn	1.577323	1.614569	
Mn	1.577179		
0	-1.329480	-1.268808	-1.117837
0	-1.329707	-1.268761	-1.117261
S	-0.975155	-0.831103	-0.712779
S	-0.975167	-0.83118	-0.753602
No of electrons	56	60	64

Bader net atomic charge =ZVAL-Bader population